CMOS Digital Integrated Circuits Silicon Monolithic

74HC4066FT

1. Functional Description

Quad Bilateral Switch

2. General

The 74HC4066FT is a high speed CMOS QUAD BILATERAL SWITCH fabricated with silicon gate CMOS technology. It consists of four independent high speed switches capable of controlling either digital or analog signals while maintaining the CMOS low power dissipation.

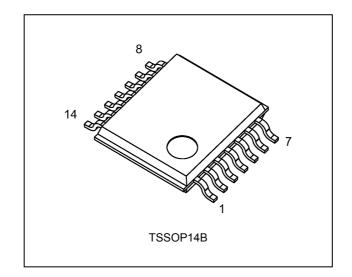
Control input (C) is provided to control the switch. The switch turns ON while the C input is high, and the switch turns OFF while low.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

3. Features

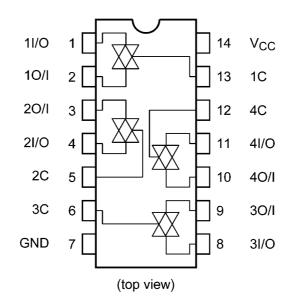
- (1) Wide operating temperature range: $T_{opr} = -40$ to 125 °C
- (2) Low power dissipation: $I_{CC} = 1.0 \ \mu A \ (max)$ at $V_{CC} = 6.0 \ V$, $T_a = 25 \ ^{\circ}C$
- (3) High noise immunity: $V_{NIH} = V_{NIL} = 28 \% V_{CC}$ (min)
- (4) Low ON resistance: $R_{ON} = 50 \Omega$ (typ.) at $V_{CC} = 9.0 V$, $V_{I/O} = V_{CC}$ or GND
- (5) High degree of linearity: THD = 0.05 % (typ.) at V_{CC} = 4.5 V

4. Packaging

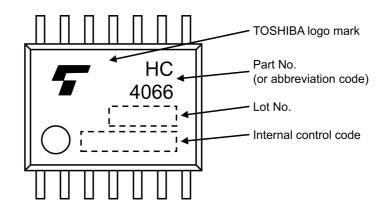


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5. Pin Assignment



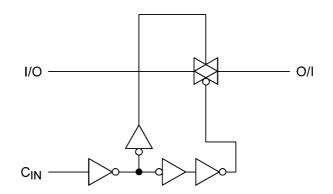
6. Marking



7. Truth Table

Control	Switch Function
Н	On
L	Off

8. System Diagram (per circuit)



9. Absolute Maximum Ratings (Note)

Characteristics	Symbol	Note	Rating	Unit
Supply voltage	V _{CC}		-0.5 to 13.0	V
Input voltage	V _{IN}		-0.5 to V _{CC} + 0.5	V
Switch I/O voltage	V _{I/O}		-0.5 to V _{CC} + 0.5	V
Input diode current	I _{IK}		±20	mA
I/O diode current	I _{I/OK}		±20	mA
Switch through current	Ι _Τ		±25	mA
V _{CC} /ground current	I _{CC}		±50	mA
Power dissipation	PD	(Note 1)	180	mW
Storage temperature	T _{stg}		-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: 180 mW in the range of $T_a = -40$ to 85 °C. From $T_a = 85$ to 125 °C a derating factor of -3.25 mW/°C shall be applied until 50 mW.

10. Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0 to 12	V
Input voltage	V _{IN}	0 to V _{CC}	V
Switch I/O voltage	V _{I/O}	0 to V _{CC}	V
Operating temperature	T _{opr}	-40 to 125	°C
Input rise and fall times	t _r ,t _f	0 to 50	μS

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either V_{CC} or GND.

11. Electrical Characteristics

11.1. DC Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Тур.	Max	Unit
High-level input voltage	VIH	_	2.0	1.50	_	_	V
			4.5	3.15	_	_]
			9.0	6.30	_	_]
			12.0	8.40	_	—	
Low-level input voltage	VIL	—	2.0	_	_	0.50	V
			4.5	—	_	1.35	
			9.0	—	_	2.70]
			12.0	—	—	3.60	
ON-resistance	R _{ON}	V _{IN} = V _{IH}	4.5	—	96	170	Ω
		$V_{I/O} = V_{CC}$ to GND $I_{I/O} \le 1 \text{ mA}$	9.0	_	55	85]
		$ 1 /0 \ge 1$ IIIA	12.0	_	45	80]
		V _{IN} = V _{IH}	2.0	—	160	—	
		$V_{I/O}$ = V_{CC} or GND $I_{I/O} \le 1 \text{ mA}$	4.5	—	70	100]
			9.0	—	50	75	
			12.0	—	45	70	
Difference of ON-resistance	ΔR_{ON}	V _{IN} = V _{IH}	4.5	—	10	30	Ω
between switches		$V_{I/O} = V_{CC}$ to GND $I_{I/O} \le 1 \text{ mA}$	9.0	—	5	12]
		II/0 ≤ 1 IIIA	12.0	_	5	10]
Input/Output leakage current (Switch OFF)	I _{OFF}	$V_{OS} = V_{CC} \text{ or GND}$ $V_{IS} = GND \text{ to } V_{CC}$ $V_{IN} = V_{IL}$	12.0	_	_	±0.1	μA
Input/Output leakage current (Switch ON, output open)	I _{I/O}	$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{IH}$	12.0	—	—	±0.1	μΑ
Control input leakage current	l _{iN}	V _{IN} = V _{CC} or GND	12.0	_	—	±0.1	μA
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND	6.0	_	_	1.0	μA
			9.0	_	_	4.0]
			12.0	_	_	8.0]

11.2. DC Characteristics (Unless otherwise specified, $T_a = -40$ to 85 °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
High-level input voltage	VIH	_	2.0	1.50	_	V
			4.5	3.15	_	
			9.0	6.30	_	7
			12.0	8.40	_	
Low-level input voltage	VIL	—	2.0	—	0.50	V
			4.5	—	1.35	
			9.0	—	2.70	
			12.0	_	3.60	
ON-resistance	R _{ON}	V _{IN} = V _{IH}	4.5	—	200	Ω
		$V_{I/O} = V_{CC}$ to GND $I_{I/O} \le 1 \text{ mA}$	9.0	—	100	
			12.0	_	90	
		$V_{IN} = V_{IH}$ $V_{I/O} = V_{CC}$ or GND $I_{I/O} \le 1 \text{ mA}$	4.5	—	130	
			9.0	—	95	
			12.0	_	90	
Difference of ON-resistance	ΔR_{ON}	$V_{IN} = V_{IH}$	4.5	—	35	Ω
between switches		$V_{I/O} = V_{CC}$ to GND $I_{I/O} \le 1 \text{ mA}$	9.0	—	15	
			12.0	_	12	
Input/Output leakage current (Switch OFF)	I _{OFF}	$V_{OS} = V_{CC} \text{ or GND}$ $V_{IS} = GND \text{ to } V_{CC}$ $V_{IN} = V_{IL}$	12.0	_	±1.0	μA
Input/Output leakage current (Switch ON, output open)	I _{I/O}	$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{IH}$	12.0	-	±1.0	μΑ
Control input leakage current	l _{iN}	V _{IN} = V _{CC} or GND	12.0	_	±1.0	μA
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND	6.0		10.0	μA
			9.0		40.0	
			12.0		80.0	

11.3. DC Characteristics (Unless otherwise specified, $T_a = -40$ to 125 °C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
High-level input voltage	V _{IH}	—	2.0	1.50	—	V
			4.5	3.15	—	
			9.0	6.30	—]
			12.0	8.40	—	
Low-level input voltage	V _{IL}	—	2.0	—	0.50	V V
			4.5	—	1.35]
			9.0	—	2.70	
			12.0	—	3.60	
ON-resistance	R _{ON}	V _{IN} = V _{IH}	4.5	—	220	Ω
		$V_{I/O} = V_{CC}$ to GND $I_{I/O} \le 1 \text{ mA}$	9.0	—	110	
			12.0	—	100	
		$V_{IN} = V_{IH}$ $V_{I/O} = V_{CC}$ or GND $I_{I/O} \le 1$ mA	4.5	—	150	
			9.0	—	110	
			12.0	—	105	
Difference of ON-resistance	ΔR_{ON}	V _{IN} = V _{IH}	4.5	—	35	Ω
between switches		$V_{I/O} = V_{CC}$ to GND $I_{I/O} \le 1 \text{ mA}$	9.0	—	15	
			12.0	—	12	
Input/Output leakage current (Switch OFF)	I _{OFF}	$V_{OS} = V_{CC} \text{ or GND}$ $V_{IS} = GND \text{ to } V_{CC}$ $V_{IN} = V_{IL}$	12.0	_	±5.0	μA
Input/Output leakage current (Switch ON, output open)	I _{I/O}	$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{IH}$	12.0	_	±5.0	μA
Control input leakage current	l _{iN}	V _{IN} = 0 to 5.5 V	12.0	—	±5.0	μA
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND	6.0		20.0	μA
			9.0	_	80.0]
			12.0	—	160.0	

11.4. AC Characteristics (Unless otherwise specified, C_L = 50 pF, T_a = 25 °C, Input: t_r = t_f = 6 ns)

Characteristics	Symbol	Note	Test Condition	V _{CC} (V)	Min	Тур.	Max	Unit
Phase difference between	Φι/Ο		_	2.0	_	10	50	ns
input to output				4.5	_	4	10	
				9.0	_	3	8	
				12.0	_	3	7	
Output enable time	t _{PZL} ,		R _L = 1 kΩ	2.0	_	18	100	ns
	t _{PZH}		See 12. AC Test Circuit, Figure 1	4.5	_	8	20	
				9.0	_	6	12	
				12.0	_	6	12	
Output disable time	t _{PLZ} ,		R _L = 1 kΩ	2.0	_	20	115	ns
	t _{PHZ}		See 12. AC Test Circuit, Figure 1	4.5	_	10	23	
				9.0	_	8	20	
				12.0	_	8	12	
Control input capacitance	C _{IN}		_	5.0	_	3		pF
Switch terminal capacitance	C _{OS}		See 12. AC Test Circuit, Figure 2	5.0	—	6	—	pF
Feedthrough capacitance	C _{IOS}		See 12. AC Test Circuit, Figure 2	5.0	—	0.5	_	pF
Power dissipation capacitance	C _{PD}	(Note 1)	See 12. AC Test Circuit, Figure 2	5.0	—	5	—	pF

Note 1: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$ (per bit)

11.5. AC Characteristics (Unless otherwise specified, C_L = 50 pF, T_a = -40 to 85 ℃, Input: t_r = t_f = 6 ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Phase difference between input to	Φι/Ο	_	2.0	_	65	ns
output			4.5	_	13	
			9.0	—	10	
			12.0	_	9	
Output enable time	t _{PZL} ,t _{PZH}	R _L = 1 kΩ	2.0	—	125	ns
		See 12. AC Test Circuit, Figure 1	4.5	—	25	
			9.0	_	22	
			12.0	—	18	
Output disable time	t _{PLZ} ,t _{PHZ}	R _L = 1 kΩ	2.0	—	145	ns
		See 12. AC Test Circuit, Figure 1	4.5	_	29	
			9.0	_	25]
			12.0		22	

11.6. AC Characteristics (Unless otherwise specified, $C_L = 50$ pF, $T_a = -40$ to 125 °C, Input: $t_r = t_f = 6$ ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Phase difference between input to	Φι/Ο		2.0	_	75	ns
output			4.5	_	15	
			9.0	_	12	
			12.0	_	11	
Output enable time	t _{PZL} ,t _{PZH}	$R_L = 1 k\Omega$	2.0	_	145	ns
		See 12. AC Test Circuit, Figure 1	4.5		29	
			9.0	_	29	
			12.0	_	22	
Output disable time	t _{PLZ} ,t _{PHZ}	R _L = 1 kΩ	2.0	_	165	ns
		See 12. AC Test Circuit, Figure 1	4.5	_	33	
			9.0	_	29	
			12.0	_	29	

11.7. Analog Switch Characteristics ($T_a = 25$ °C) (Note)

Characteristics	Symbol	Test Condition	Test Condition			Unit
Sine Wave Distortion	THD	R _L = 10 kΩ, C _L = 50 pF, f _{IN} = 1 kHz	V _{IN} = 4.5 V _{p-p}	4.5	0.05	%
			V _{IN} = 9.0 V _{p-p}	9.0	0.04	
Maximum frequency response (switch ON)	f _{MAX(I/O)}	V_{IN} is centered at (V _{CC} /2). Adjust input for 0dBm. Increase f_{IN} frequency until dB meter reads -3dB.		4.5	200	MHz
		$R_L = 50 \Omega$, $C_L = 10 pF$, $f_{IN} = 1 MHz$, sine wave See 12. AC Test Circuit, Figure 3		9.0	200	
Feed through attenuation (switch OFF)	FTH	V_{IN} is centered at (V _{CC} /2). Adjust input for 0dBm.		4.5	-60	dB
	R_L = 600 Ω, C_L = 50 pF, $f_{ N}$ = 1 MHz, sine wave See 12. AC Test Circuit, Figure 4			9.0	-60	
Crosstalk (control input to signal output)	X _{talk}	R_L = 600 Ω, C_L = 50 pF, f_{IN} = 1 MHz,		4.5	60	mV
		square wave (t _r = t _f = 6 ns) See 12. AC Test Circuit, Figure 5		9.0	100	
Crosstalk (between any switches)	X _{talk}	V_{IN} is centered at ($V_{CC}/2$). Adjust input for 0dBm.		4.5	-60	dB
	R_L = 600 Ω, C_L = 50 pF, f _{IN} = 1 MHz, sine wave See 12. AC Test Circuit, Figure			9.0	-60	

Note: These characteristics are determined by design of devices.

12. AC Test Circuit

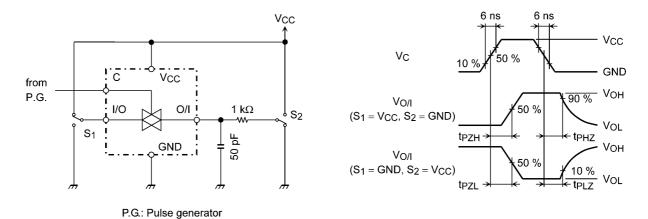


Figure 1 tPLZ, tPHZ, tPZL, tPZH

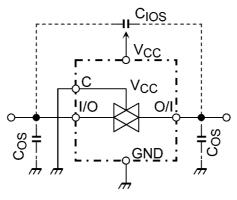


Figure 2 CIOS, COS

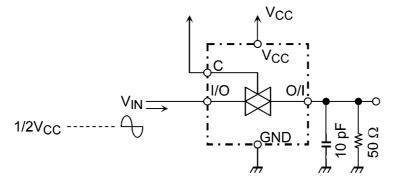


Figure 3 Frequency Response (switch on)

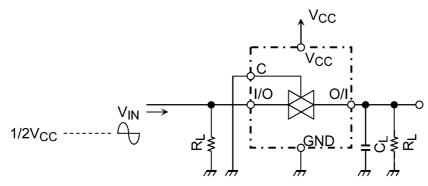


Figure 4 Feedthrough

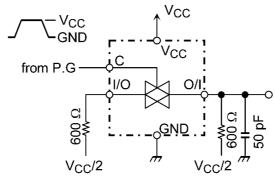


Figure 5 Cross Talk (control input to output signal)

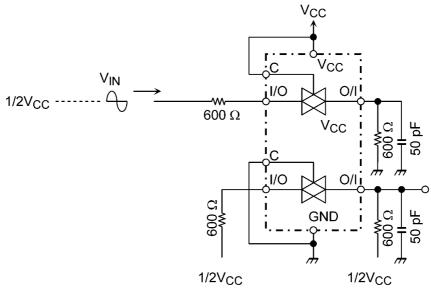
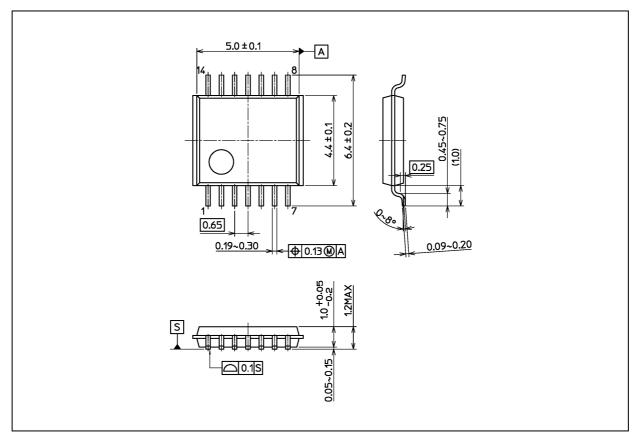


Figure 6 Cross Talk (between any two switches)

74HC4066FT

Package Dimensions

Unit: mm



Weight: 0.054 g (typ.)

Package Name(s)			
Nickname: TSSOP14B			

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